BAW56LT1

Preferred Device

Monolithic Dual Switching Diode Common Anode

ON Semiconductor®

http://onsemi.com

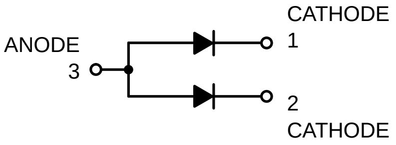
MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Non−Repetitive Peak Forward Current t = 1 μs (Note 3)	I_{FSM}	4	A

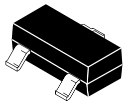
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

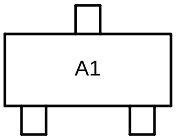
1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
3. Square Wave; T_j = 25°C.



MARKING DIAGRAM



SOT−23(TO−236)
CASE 318
Style 12



A1 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
BAW56LT1	SOT−23	3000 / Tape & Reel
BAW56LT3	SOT−23	10,000 / Tape & Reel

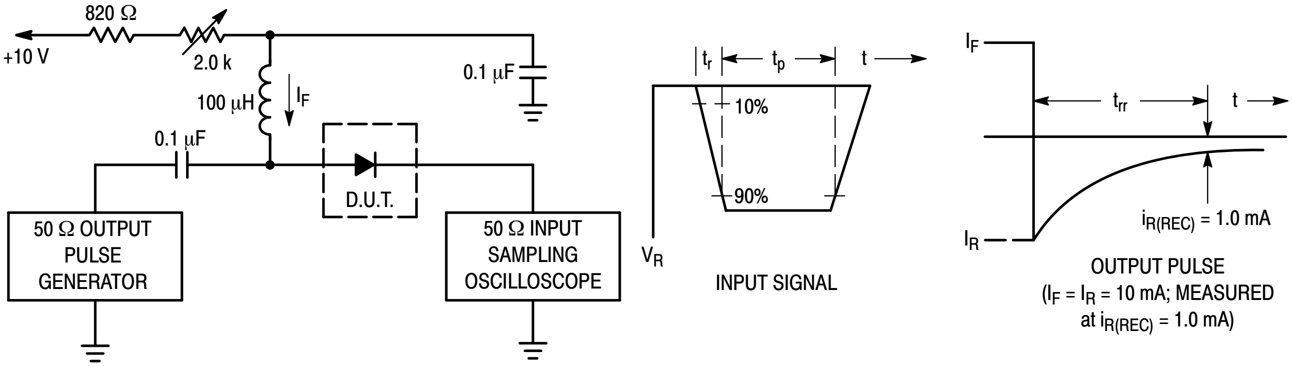
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

February, 2004 − Rev. 3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) **(EACH DIODE)**

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	70	–	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc, T_J = 150°C) (V_R = 70 Vdc) (V_R = 70 Vdc, T_J = 150°C)	I_R	 – – –	 30 2.5 50	μAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	2.0	pF
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 150 mAdc)	V_F	 – – – –	 715 855 1000 1250	mVdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc) (Figure 1) R_L = 100 Ω	t_{rr}	–	6.0	ns



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

Curves Applicable to Each Cathode

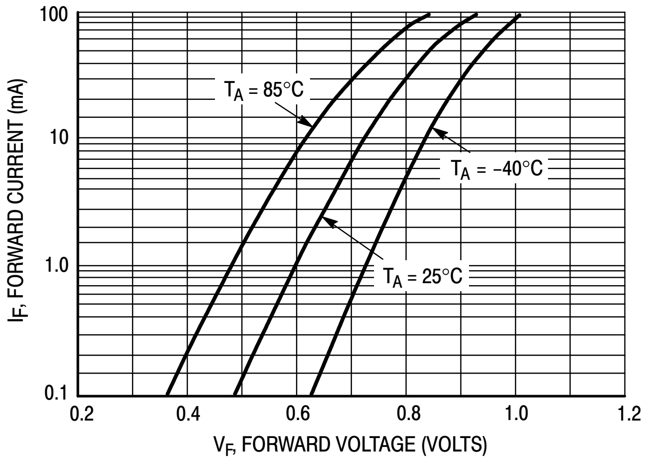


Figure 2. Forward Voltage

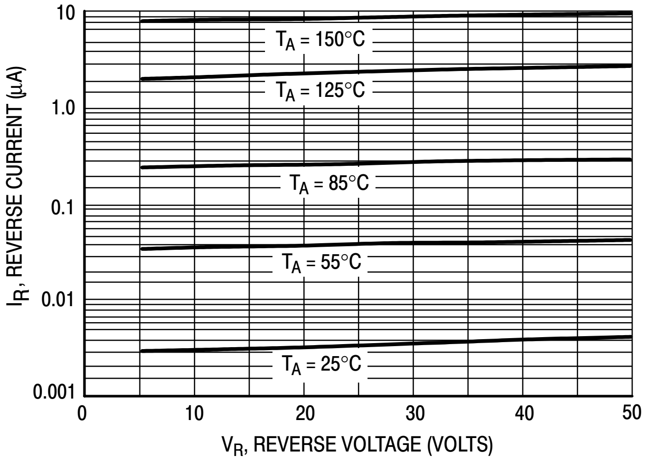


Figure 3. Leakage Current

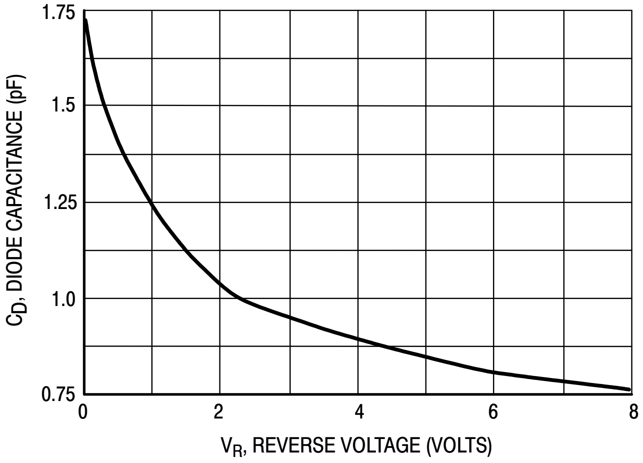
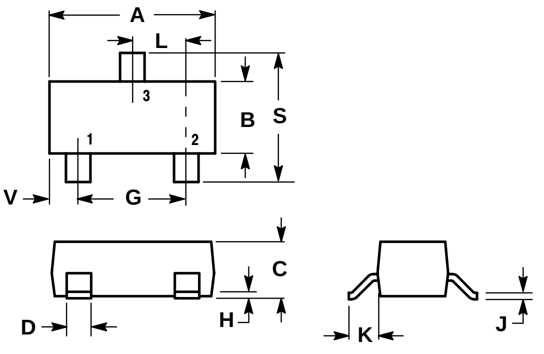


Figure 4. Capacitance

PACKAGE DIMENSIONS

SOT−23−3 (TO−236)

CASE 318−08
ISSUE AH



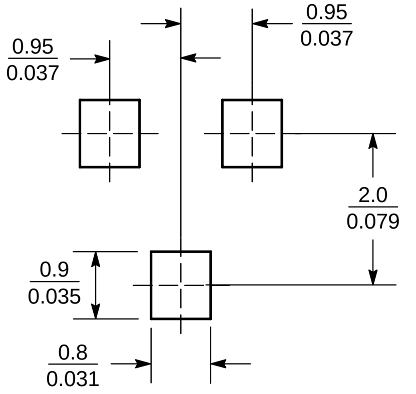
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−03 AND −07 OBSOLETE, NEW STANDARD 318−08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

SOLDERING FOOTPRINT



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

SOT−23−3

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